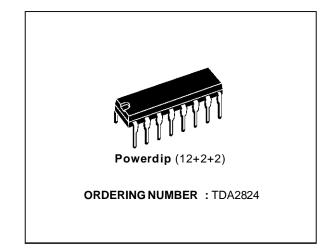


DUAL POWER AMPLIFIER

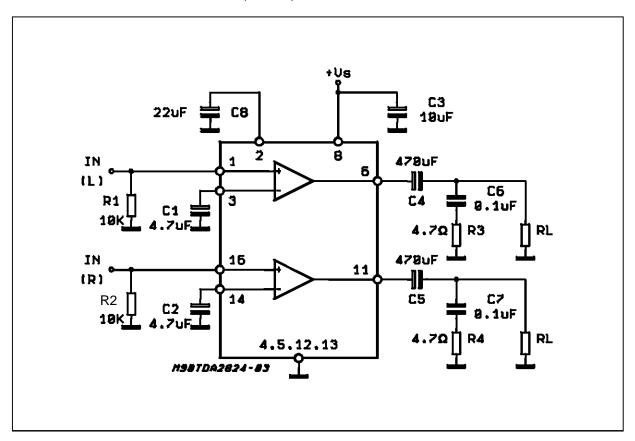
- SUPPLY VOLTAGE DOWN TO 3 V
- HIGH SVR
- LOW CROSSOVER DISTORTION
- LOW QUIESCENT CURRENT
- BRIDGE OR STEREO CONFIGURATION



DESCRIPTION

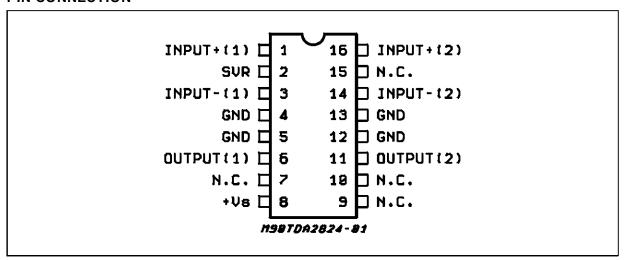
The TDA2824 is a monolithic integrated circuit in 12+2+2 powerdip, intended for use as dual audio power amplifier in portable radios and TV sets.

TYPICAL APPLICATION CIRCUIT (Stereo)

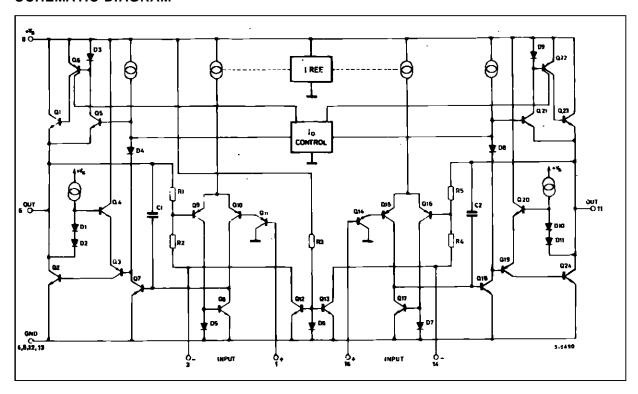


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PIN CONNECTION



SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vs	Supply Voltage	16	V
lo	Output Peak Current	1.5	Α
P _{tot}	Total Power Dissipation at $T_{amb} = 50^{\circ}C$ $T_{amb} = 70^{\circ}C$	1.25 4	W W
T _{stg} , T _j	Storage and Junction Temperature	-40 to 150	°C



THERMAL DATA

Symbol	Parameter	Value	Unit
R _{th j-amb}	Thermal Resistance Junction-ambient Max.	80	°C/W
R _{th j-case}	Thermal Resistance Junction-case Max.	20	°C/W

ELECTRICAL CHARACTERISTICS ($V_S = 6V$, $T_{amb} = 25$ °C, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit	
STEREO (test circuit of fig. 1)							
Vs	Supply Voltage		3		15	V	
Vo	Quiescent Output Voltage	V _S = 9V V _S = 9V		4 2.7		V V	

Vo	Quiescent Output Voltage	$V_S = 9V$ $V_S = 9V$		4 2.7		V V	
I _d	Quiescent Drain Current				6	12	mA
I _b	Input Bias Current				100		nA
Po	Output Power (each channel)			1.3 0.45	1.7 0.65 0.32		W W W
d	Distortion	$V_S = 9V$, $f = 1KHz$ $R_L = 8\Omega$, $P_O = 0.5W$			0.2		%
G _V	Closed Loop Voltage Gain	f = 1KHz		36	39	41	dB
Ri	Input Resistance	f = 1KHz		100			ΚΩ
e _N	Total Input Noise	$R_S = 10K\Omega$	B = 22Hz to 22KHz		2.5		μV
			Curve A		2		μV
SVR	Supply Voltage Rejection	f = 100Hz		40	50		dB
CS	Channel Separation	$R_S = 10K\Omega$ $f = 1KHz$			50		dB

BRIDGE (test circuit of fig. 2)

Vs	Supply Voltage			3		15	V
Vos	Output Offset Voltage	$R_1 = 8\Omega$		 		60	mV
I _b	Imput Bias Current				100		nA
Po	Output Power	d = 10% V _S = 9V V _S = 6V V _S = 4.5V	$f = 1KHz$ $R_L = 8\Omega$ $R_L = 8\Omega$ $R_L = 4\Omega$	2.5 0.9	3.2 1.35 1		W W W
d	Distortion (f = 1KHz)	$R_L = 8\Omega$	P _O = 0.5W		0.2		%
Gv	Closed Loop Voltage Gain	f = 1KHz			39		dB
e _N	Total Input Noise	R _S = 10KΩ	B = 22Hz to 22KHz		3		mV
			Curve A		2.5		μV
SVR	Supply Voltage Rejection	f = 100Hz		48	60		dB

Figure 1: Test Circuit (stereo).

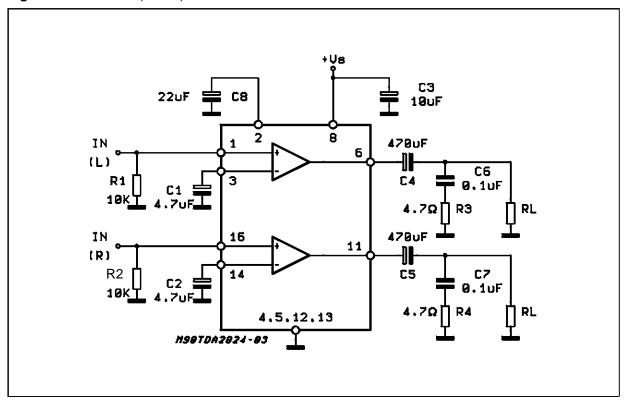


Figure 2: P.C. Board and Component Layout of the Circuit of Figure 1. (1:1 scale)

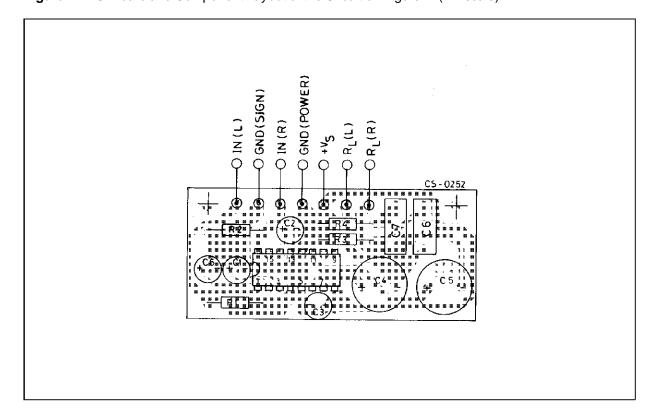


Figure 3: Test Circuit (bridge).

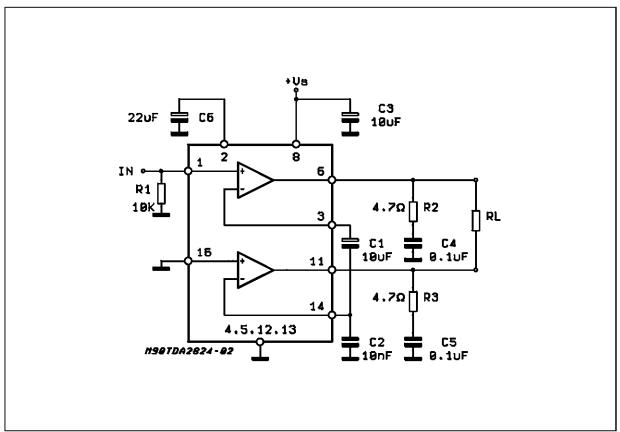


Figure 4: P.C. Board and Component Layout of the Circuit of Figure 3. (1:1 scale)

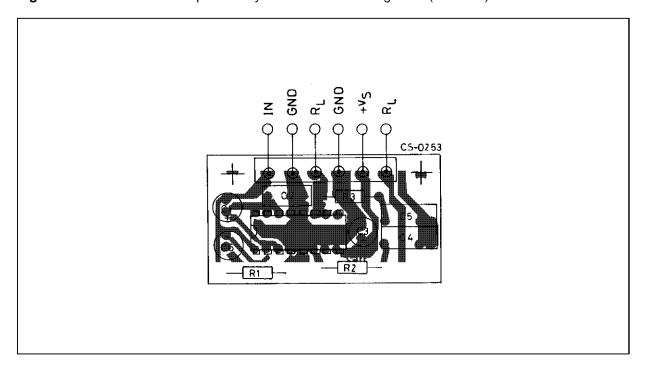


Figure 3 : Output Power vs. Supply Voltage (Stereo).

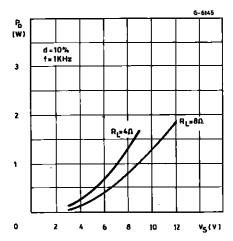


Figure 5: Distortion vs. Output Power (Bridge).

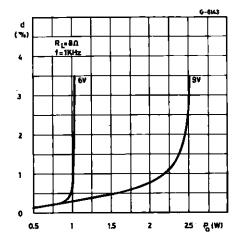


Figure 7 : Supply Voltage Rejection vs. Frequency (Stereo)

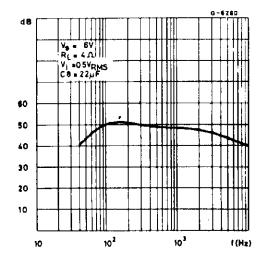


Figure 4 : Output Power vs. Supply Voltage (Bridge).

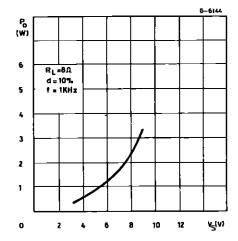


Figure 6 : Distortion vs. Output Power (Bridge).

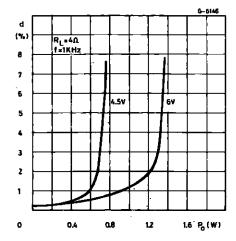


Figure 8 : Quiescent Current vs. Supply Voltage.

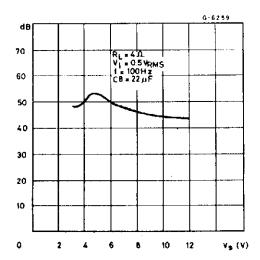


Figure 9: Quiescent Current vs. Supply Voltage.

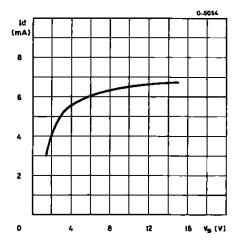


Figure 11 : Total Power Dissipation vs. Output Power (Bridge).

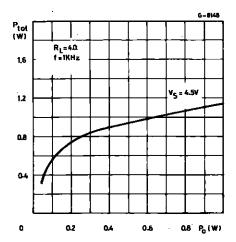


Figure 10 : Total Power Dissipation vs. Output Power (Stereo).

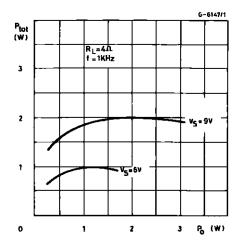
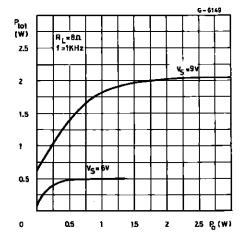


Figure 12 : Total Power Dissipation vs. Output Power (Bridge).

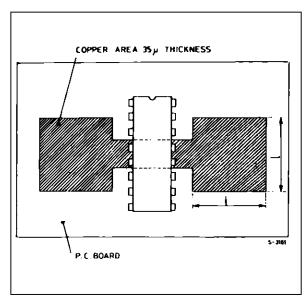


MOUNTING INSTRUCTION

The R_{th j-amb} of the TDA2824 can be reduced by soldering the GND pins to a suitable copper area of the printed circuit board (Figure 13) or to an external heatsink (Figure 14).

The diagram of Figure 15 shows the maximum dissipable power P_{tot} and the $R_{th\,j\text{-amb}}$ as a function of the side " ∂ " of two equal square copper areas having a thickness of 35 μ (1.4 mils).

Figure 13 : Example of P.C. Board Copper Area which is used as Heatsink.



During soldering the pins temperature must not exceed 260 °C and the soldering time must not be longer than 12 seconds.

The external heatsink or printed circuit copper area must be connected to electrical ground.

Figure 14: External Heatsink Mounting Example.

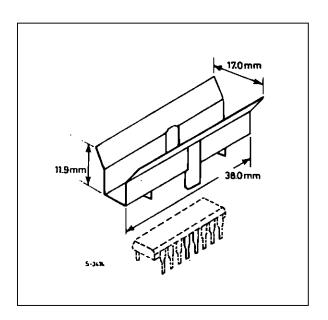


Figure 15: Maximum Dissipable Power and Junction to Ambient Thermal Resistance vs. Side "∂".

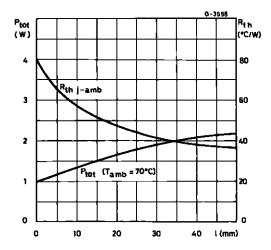
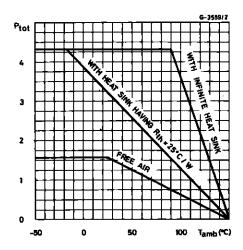
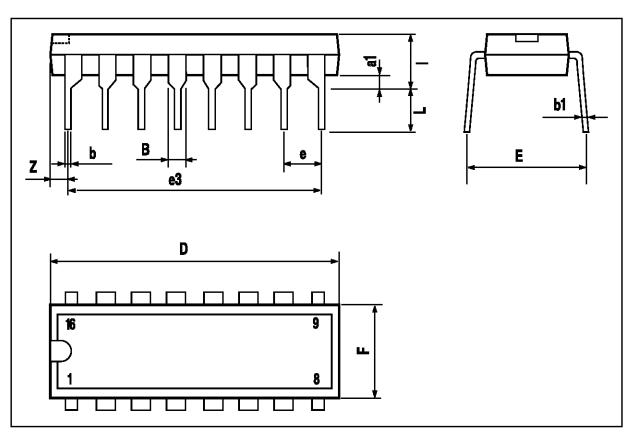


Figure 16 : Maximum Allowable Power Dissipation vs. Ambient Temperature.



POWERDIP 12+2+2 PACKAGE MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
a1	0.51			0.020			
В	0.85		1.40	0.033		0.055	
b		0.50			0.020		
b1	0.38		0.50	0.015		0.020	
D			20.0			0.787	
E		8.80			0.346		
е		2.54			0.100		
e3		17.78			0.700		
F			7.10			0.280	
I			5.10			0.201	
L,		3.30			0.130		
Z			1.27			0.050	



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